

## Sixpack

### SKiiP 13AC12T7V1

### Features\*

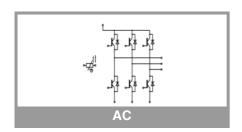
- 1200V Generation 7 IGBTs (T7)
- · Robust and soft switching freewheeling diodes in CAL technology
- · Highly reliable spring contacts for electrical connections
- UL recognized: File no. E63532

### **Remarks**

- · Max. case temperature limited to T<sub>C</sub>=T<sub>S</sub>=125 °C
- Product reliability results valid for  $T_j{\le}150~^{\circ}C$  (recommended T<sub>j,op</sub>=-40...+150 °C)
  • MiniSKiiP "Technical Explanations"
- and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.
- For storage and case temperature with TIM see document: "Technical **Explanations Thermal Interface** Materials"

Maximum Ratings	s		
Conditions		Values	Unit
IGBT		•	
T <sub>j</sub> = 25 °C		1200	V
λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 70 °C	37	Α
T <sub>j</sub> = 175 °C	T <sub>s</sub> = 100 °C	31	Α
λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 70 °C	41	Α
T <sub>j</sub> = 175 °C	T <sub>s</sub> = 100 °C	34	Α
		25	Α
		50	Α
		-20 20	V
$V_{CC} = 800 \text{ V}$ $V_{GE} \le 15 \text{ V}$ $V_{CES} \le 1200 \text{ V}$	T <sub>j</sub> = 175 °C	7	μs
		-40 175	°C
Diode			,
λ <sub>paste</sub> =0.8 W/(mK)	T <sub>s</sub> = 70 °C	27	Α
T <sub>j</sub> = 175 °C	T <sub>s</sub> = 100 °C	22	Α
λ <sub>paste</sub> =2.5 W/(mK)	T <sub>s</sub> = 70 °C	30	Α
T <sub>j</sub> = 175 °C	T <sub>s</sub> = 100 °C	24	Α
		50	Α
$t_p = 10 \text{ ms}, \sin 180^\circ$	°, T <sub>j</sub> = 150 °C	100	Α
		-40 175	°C
•		•	•
T <sub>terminal</sub> = 80 °C, 20	A per spring	40	Α
module without TIN	Л	-40 125	°C
AC sinus 50 Hz, t =	1 min	2500	V
	$\begin{tabular}{ c c c c } \hline \textbf{Conditions} \\ \hline \textbf{IGBT} \\ \hline $T_j = 25 \text{ °C}$ \\ $\lambda_{paste} = 0.8 \text{ W/(mK)}$ \\ $T_j = 175 \text{ °C}$ \\ $\lambda_{paste} = 2.5 \text{ W/(mK)}$ \\ \hline $T_j = 175 \text{ °C}$ \\ \hline $V_{CE} = 800 \text{ V}$ \\ $V_{GE} \le 15 \text{ V}$ \\ $V_{CES} \le 1200 \text{ V}$ \\ \hline \end{tabular} \\ \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{ c c c c } \hline \textbf{Conditions} & \textbf{Values} \\ \hline \textbf{IGBT} \\ \hline \hline T_j = 25  ^{\circ}\text{C} & 1200 \\ \hline \lambda_{paste} = 0.8  \text{W/(mK)} & T_s = 70  ^{\circ}\text{C} & 37 \\ \hline T_j = 175  ^{\circ}\text{C} & T_s = 100  ^{\circ}\text{C} & 31 \\ \hline \lambda_{paste} = 2.5  \text{W/(mK)} & T_s = 70  ^{\circ}\text{C} & 41 \\ \hline T_j = 175  ^{\circ}\text{C} & T_s = 100  ^{\circ}\text{C} & 34 \\ \hline \hline V_{CE} = 175  ^{\circ}\text{C} & T_s = 100  ^{\circ}\text{C} & 34 \\ \hline \hline V_{CE} \leq 15  \text{V} & T_j = 175  ^{\circ}\text{C} & 7 \\ \hline \hline V_{CES} \leq 1200  \text{V} & T_j = 175  ^{\circ}\text{C} & 7 \\ \hline \hline Diode & & 27 \\ \hline \hline T_j = 175  ^{\circ}\text{C} & T_s = 100  ^{\circ}\text{C} & 22 \\ \hline \lambda_{paste} = 0.8  \text{W/(mK)} & T_s = 70  ^{\circ}\text{C} & 22 \\ \hline \lambda_{paste} = 2.5  \text{W/(mK)} & T_s = 70  ^{\circ}\text{C} & 30 \\ \hline T_j = 175  ^{\circ}\text{C} & T_s = 100  ^{\circ}\text{C} & 24 \\ \hline \hline \hline t_p = 10  \text{ms, sin } 180  ^{\circ},  T_j = 150  ^{\circ}\text{C} & 100 \\ \hline \hline T_{terminal} = 80  ^{\circ}\text{C},  20  \text{A per spring} & 40 \\ \hline \text{module without TIM} & -40   125 \\ \hline \end{array} $

Characteristics							
Symbol	Conditions	min.	typ.	max.	Unit		
Inverter -	Inverter - IGBT						
V <sub>CE(sat)</sub>	I <sub>C</sub> = 25 A	T <sub>j</sub> = 25 °C		1.60	1.75	V	
	V <sub>GE</sub> = 15 V	T <sub>j</sub> = 150 °C		1.82	1.96	V	
	chiplevel	T <sub>j</sub> = 175 °C		1.86	2.00	V	
$V_{CE0}$		T <sub>j</sub> = 25 °C		0.90	1.00	V	
	chiplevel	T <sub>j</sub> = 150 °C		0.75	0.83	V	
		T <sub>j</sub> = 175 °C		0.72	0.80	V	
r <sub>CE</sub>	V 15 V	T <sub>j</sub> = 25 °C		28	30	mΩ	
	V <sub>GE</sub> = 15 V chiplevel	T <sub>j</sub> = 150 °C		43	45	mΩ	
	o inprovor	T <sub>j</sub> = 175 °C		46	48	mΩ	
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_{C} = 0.5$	3 mA	5.15	5.8	6.45	V	
I <sub>CES</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 12$	200 V, $T_j = 25 ^{\circ}\text{C}$			1	mA	
C <sub>ies</sub>	V <sub>CE</sub> = 25 V V <sub>GE</sub> = 0 V	f = 1 MHz		4.80		nF	
C <sub>oes</sub>		f = 1 MHz		0.06		nF	
C <sub>res</sub>		f = 1 MHz		0.02		nF	
$Q_G$	V <sub>GE</sub> = - 8V + 15 V			350		nC	
R <sub>Gint</sub>	T <sub>j</sub> = 25 °C			0		Ω	





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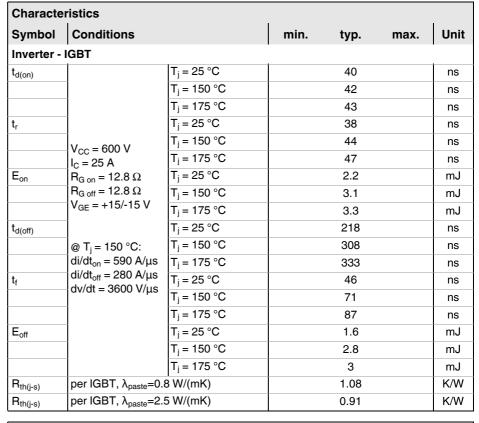
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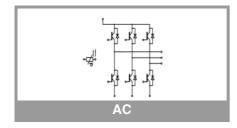
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Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
Inverse - Diode								
$V_F = V_{EC}$	I <sub>F</sub> = 25 A	T <sub>j</sub> = 25 °C		2.41	2.74	V		
	$V_{GE} = 0 V$	T <sub>j</sub> = 150 °C		2.45	2.79	V		
	chiplevel	T <sub>j</sub> = 175 °C		2.30	2.62	V		
$V_{F0}$		T <sub>j</sub> = 25 °C		1.30	1.50	V		
	chiplevel chiplevel $I_F = 25 \text{ A}$ $V_{GE} = +15/-15 \text{ V}$ $V_{CC} = 600 \text{ V}$	T <sub>j</sub> = 150 °C		0.90	1.10	V		
		T <sub>j</sub> = 175 °C		0.82	0.98	V		
r <sub>F</sub>		T <sub>j</sub> = 25 °C		44	50	mΩ		
	chiplevel	T <sub>j</sub> = 150 °C		62	68	mΩ		
		T <sub>j</sub> = 175 °C		59	66	mΩ		
I <sub>RRM</sub>		T <sub>j</sub> = 25 °C		15		Α		
	V <sub>GE</sub> = +15/-15 V	T <sub>j</sub> = 150 °C		20		Α		
		T <sub>j</sub> = 175 °C		23		Α		
Q <sub>rr</sub>		T <sub>j</sub> = 25 °C		1.5		μC		
	V <sub>CC</sub> = 600 V	T <sub>j</sub> = 150 °C		3.7		μC		
	@ T <sub>i</sub> = 150 °C:	T <sub>j</sub> = 175 °C		4.1		μC		
E <sub>rr</sub>	di/dt <sub>off</sub> = 610 A/μs	T <sub>j</sub> = 25 °C		0.45		mJ		
		T <sub>j</sub> = 150 °C		1.4		mJ		
		T <sub>j</sub> = 175 °C		1.8		mJ		
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =0	.8 W/(mK)		1.38		K/W		
R <sub>th(j-s)</sub>	per Diode, λ <sub>paste</sub> =2	.5 W/(mK)		1.18		K/W		
Module								
L <sub>CE</sub>				-		nΗ		
Ms	to heat sink		2		2.5	Nm		
w				30		g		





Characteristics							
Symbol	Conditions	min.	typ.	max.	Unit		
Temperati	ure Sensor						
R <sub>100</sub>	T <sub>r</sub> =100°C (R <sub>25</sub> =1000Ω)		1670 ± 3%		Ω		
R <sub>(T)</sub>	$\begin{aligned} &R_{(T)}{=}1000\Omega[1{+}A(T{-}25^{\circ}C){+}B(T{-}25^{\circ}C)^{2}]\\ , &A=7.635^{*}10^{-3\circ}C^{-1},\\ &B=1.731^{*}10^{-5\circ}C^{-2} \end{aligned}$						

Creepage distance (spring to spring) between temperature sensor and phase W = 2.9 mm (CTI 600)

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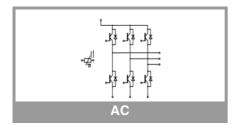
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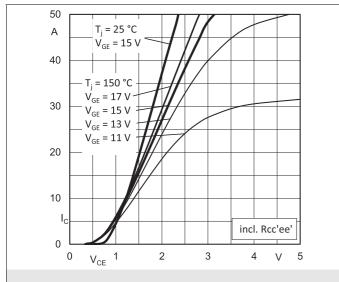
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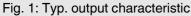
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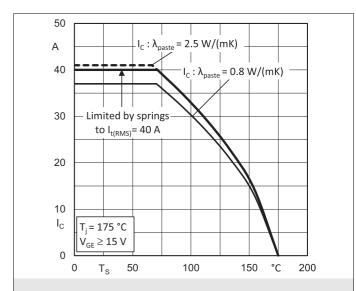


Fig. 2: Rated current vs. temperature  $I_C = f(T_S)$ 

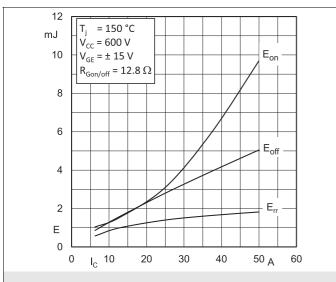


Fig. 3: Typ. turn-on /-off energy =  $f(I_C)$ 

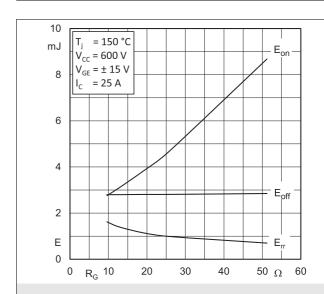


Fig. 4: Typ. turn-on /-off energy = f (R<sub>G</sub>)

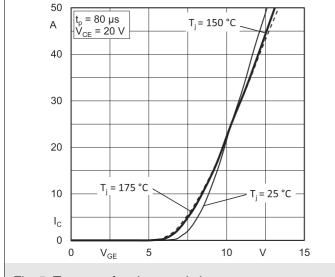


Fig. 5: Typ. transfer characteristic

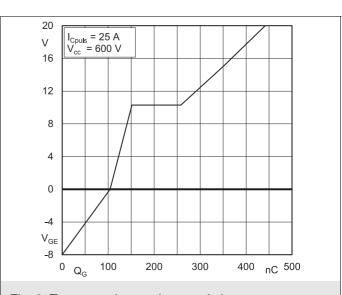
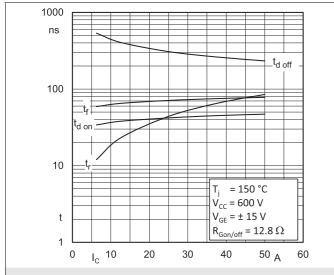
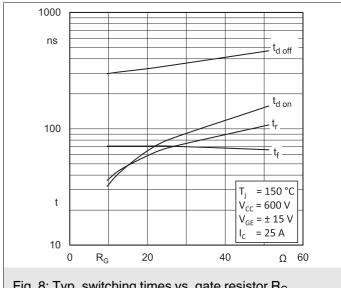
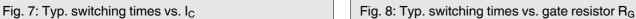
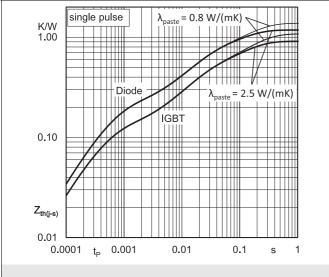


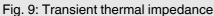
Fig. 6: Typ. gate charge characteristic











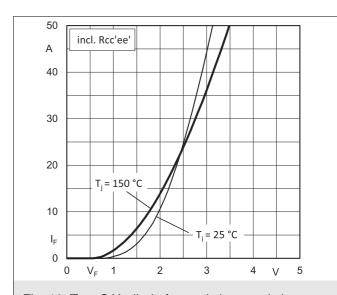


Fig. 10: Typ. CAL diode forward characteristic

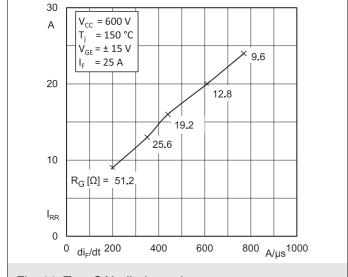


Fig. 11: Typ. CAL diode peak reverse recovery current

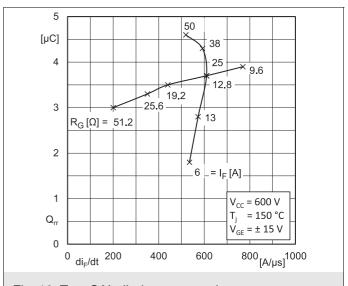
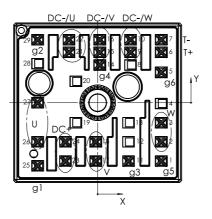


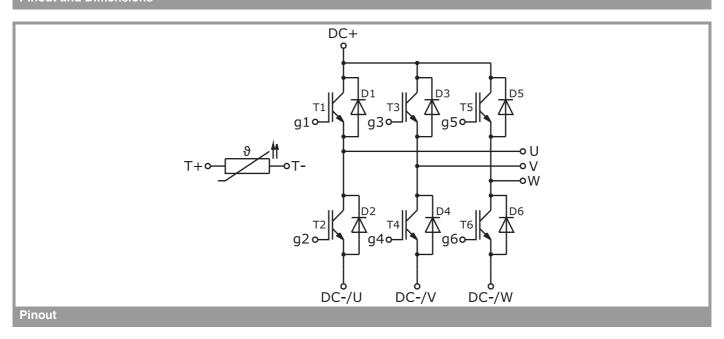
Fig. 12: Typ. CAL diode recovery charge

Pin out							
Pin	Χ	Υ	Function	Pin	Х	Υ	Function
1	15,93	-14,6	g5	16	0,53	15,8	DC-/V
2	15,93	-9,8	W	17	-0,48	-14,6	V
3	15,93	-5	W	18	-0,48	<del>-</del> 9,8	V
4				19			
5	15,93	7,63	g6	20			
6	15,93	12,63	T+	21	-7,18	12,63	DC-/U
7	15,93	15,8	T-	22	-7,18	15,8	DC-/U
8				23	-8,08	-14,6	DC+
9	8,23	12,63	DC-/W	24	-8,08	<del>-</del> 9,8	DC+
10	8,23	15,8	DC-/W	25	-15,03	-15,8	g1
11	7,73	-14,6	g3	26	-15,03	<del>-</del> 9,8	U
12				27	-15,03	0	U
13				28			
14	0,53	9,45	g4	29	-15,03	15,8	g2
15	0,53	12,63	DC-/V				

all values in mm



### **Pinout and Dimensions**



This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

#### \*IMPORTANT INFORMATION AND WARNINGS

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